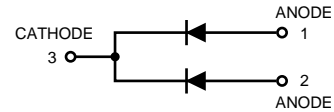
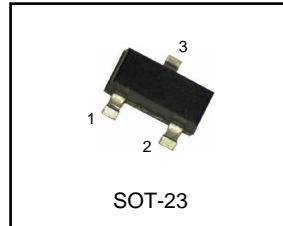


## Monolithic Dual Switching Diode

**BAV74**



### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	VR	50	Vdc
Peak Forward Current	IF	200	mAdc
Peak Forward Surge Current	IFM( surge )	500	mAdc

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max.	Unit
Total Device Dissipation FR-5 Board <sup>(1)</sup> TA=25°C Derate above 25°C	PD	225 1.8	mW mW / °C
Thermal Resistance, Junction to Ambient	R $\theta$ JA	556	°C / W
Total Device Dissipation Alumina Substrate, <sup>(2)</sup> TA=25°C Derate above 25°C	PD	300 2.4	mW mW / °C
Thermal Resistance, Junction to Ambient	R $\theta$ JA	417	°C / W
Junction and Storage Temperature	TJ,TSTG	-55 to +150	°C

### DEVICE MARKING

**BAV74=JA**

### ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min.	Max.	Unit
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### OFF CHARACTERISTICS

Reverse Breakdown Voltage ( IBR=5.0 uAdc )	V(BR)	50	-	Vdc
Forward Voltage ( IF=100 mAdc )	VF	-	1000	mVdc
Reverse Voltage Leakage Current ( VR=50 Vdc ) ( VR=50 Vdc, TJ=125°C )	IR	- -	0.1 100	uAdc
Diode Capacitance ( VR=0, f=1.0MHz )	CJ	-	2.0	pF
Reverse Recovery Time ( IF=IR=10 mAdc, IR(REC)=1.0mAdc, measured at IR=1.0mA RL=100 Ω )	trr	-	4.0	nS

(1) FR-5=1.0 x 0.75 x 0.062in.

(2) Alumina=0.4 x 0.3 x 0.024in. 99.5% alumina.

FIGURE 1. FORWARD VOLTAGE

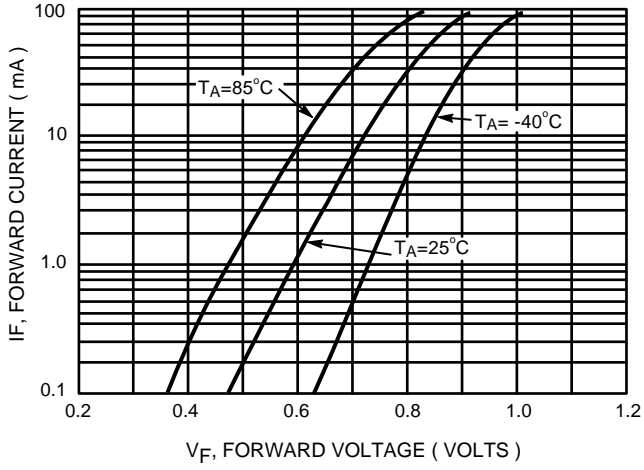


FIGURE 2. LEAKAGE CURRENT

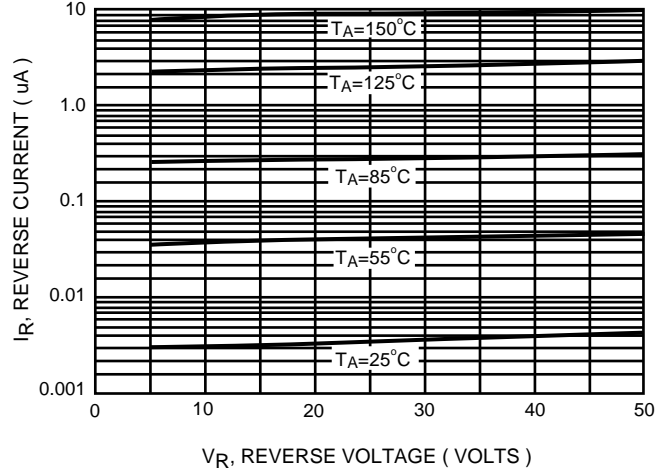


FIGURE 3. CAPACITANCE

